



SANYO Semiconductors

DATA SHEET

2SC6099

NPN Epitaxial Planar Silicon Transistor

High-Voltage Switching Applications

Applications

- DC / DC converter, relay drivers, lamp drivers, motor drivers, inverter.

Features

- Adoption of FBET, MBIT process.
- High current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.
- High allowable power dissipation.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		120	V
Collector-to-Emitter Voltage	VCE		120	V
Collector-to-Emitter Voltage	VCEO		100	V
Emitter-to-Base Voltage	VEBO		6.5	V
Collector Current	IC		2	A
Collector Current (Pulse)	ICP		3	A
Base Current	IB		400	mA
Collector Dissipation	PC		0.8	W
		Tc=25°C	15	W
Junction Temperature	TJ		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	ICBO	VCB=80V, IE=0A			1	μA
Emitter Cutoff Current	IEBO	VEB=4V, IC=0A			1	μA
DC Current Gain	hFE	VCE=5V, IC=100mA	300		600	

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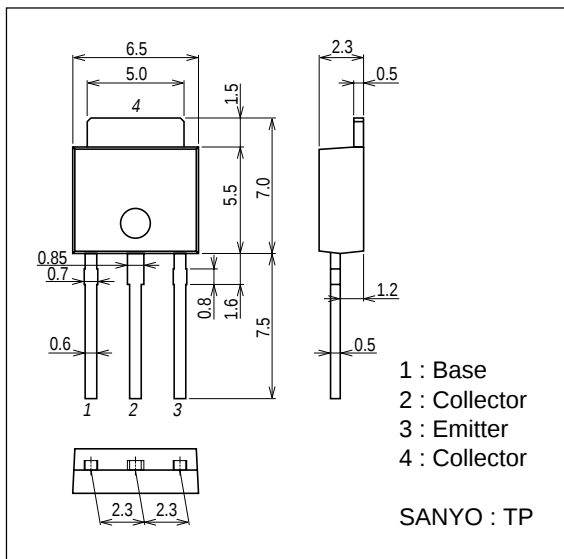
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=300mA$		300		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$		13		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1A, I_B=100mA$		110	165	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=1A, I_B=100mA$		0.9	1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0A$	120			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=100\mu A, R_{BE}=0\Omega$	120			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	100			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0A$	6.5			V
Turn-ON Time	t_{on}	See specified Test Circuit.		40		ns
Storage Time	t_{stg}	See specified Test Circuit.		1100		ns
Fall Time	t_f	See specified Test Circuit.		40		ns

Package Dimensions

unit : mm

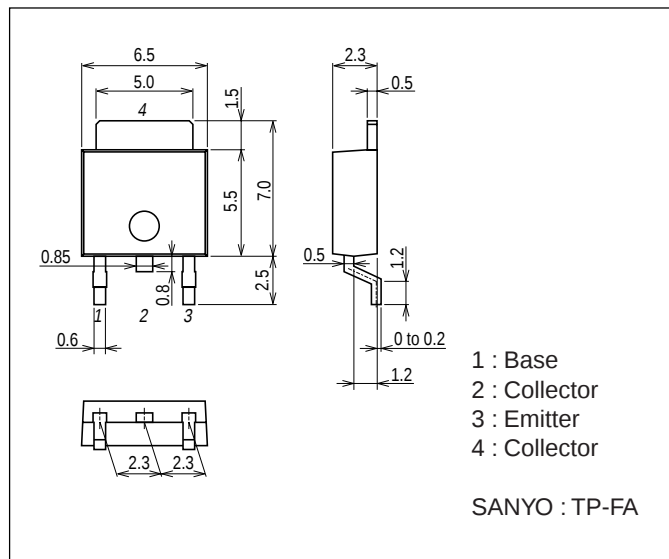
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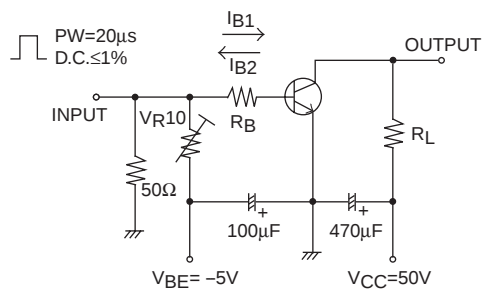
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unit : mm

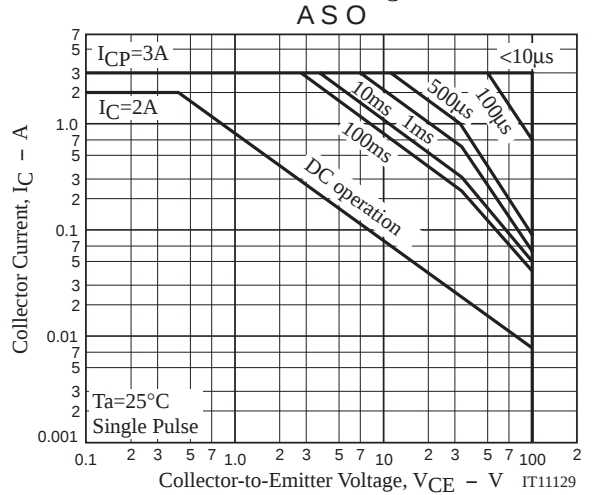
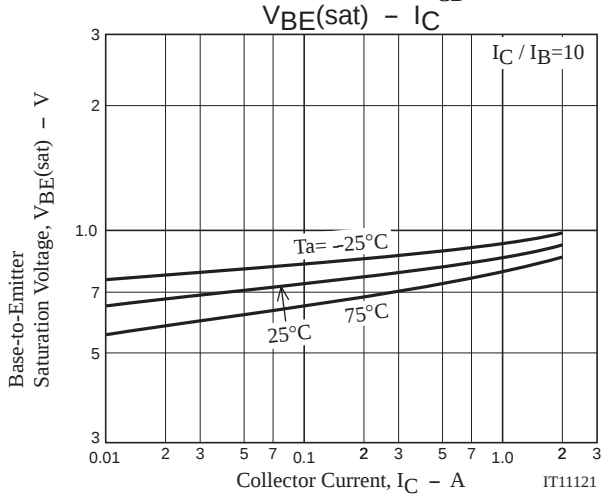
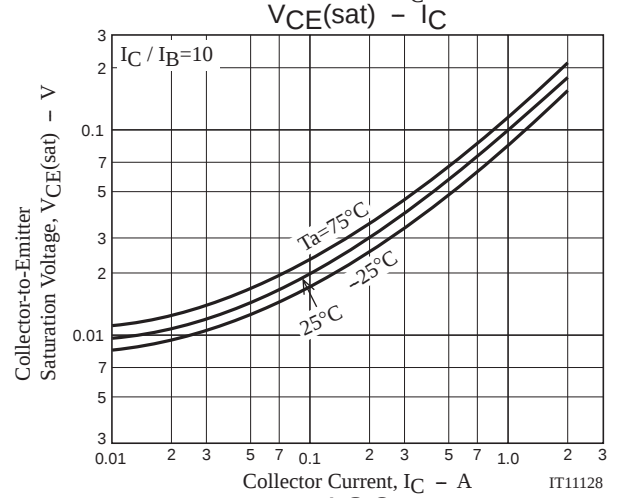
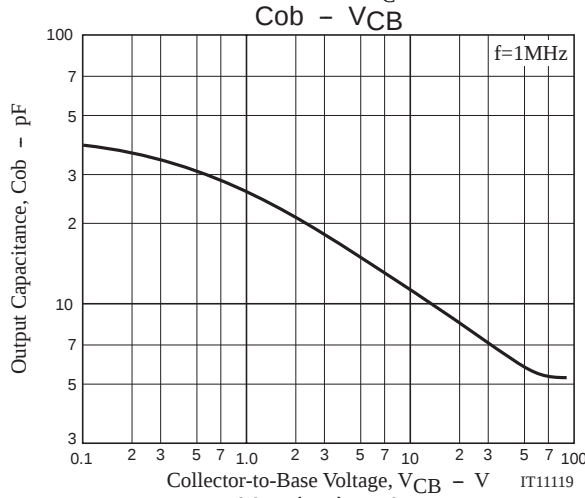
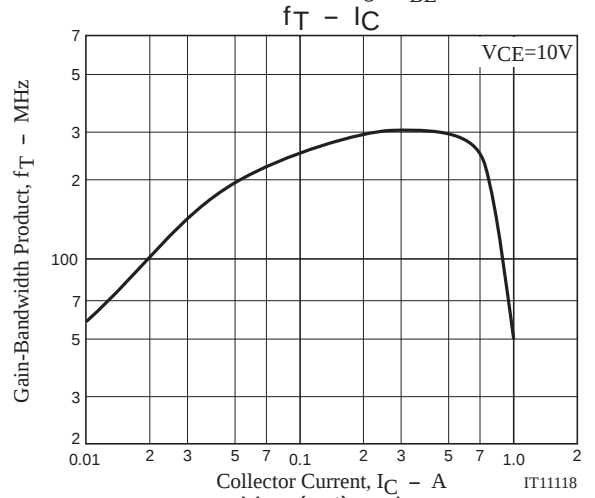
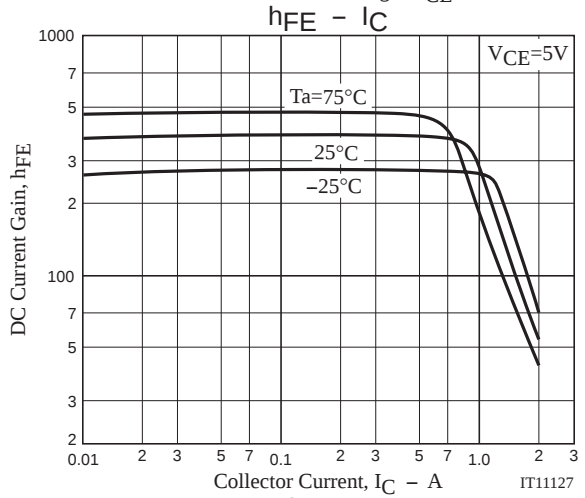
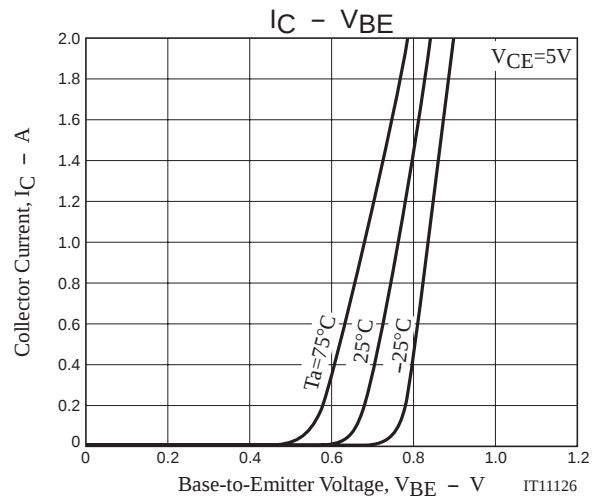
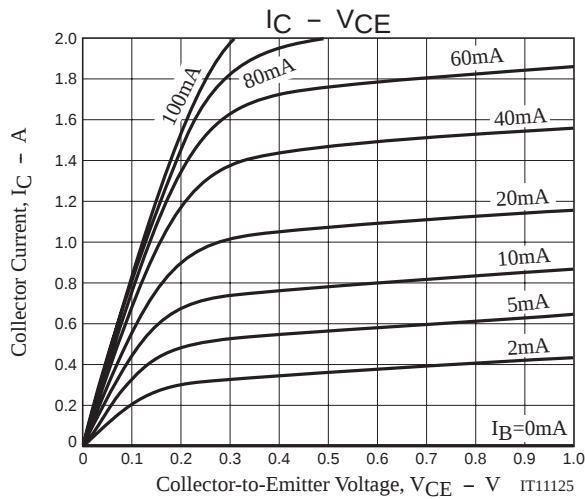
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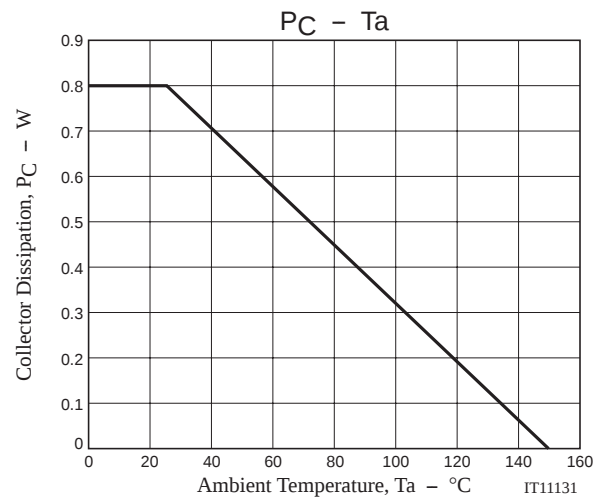
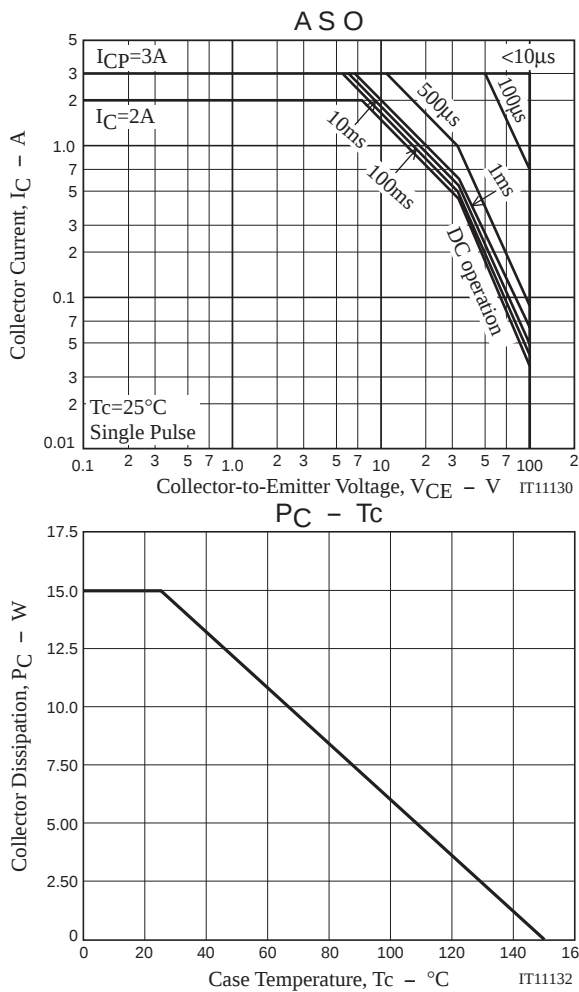


Switching Time Test Circuit



$$10I_{B1}=-10I_{B2}=I_C=0.5A$$





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